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(54) Title: METHOD OF MITIGATING SUBSTRATE DAMAGE DURING DEPOSITION PROCESSES

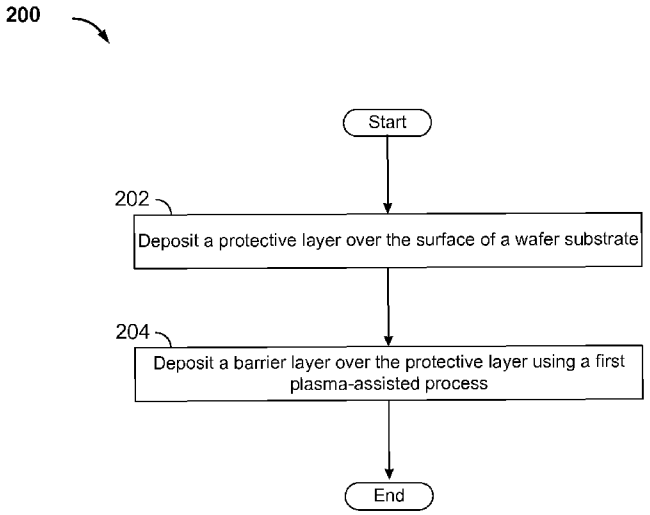


Figure 1

(57) Abstract: Systems, methods, and apparatus for depositing a protective layer on a wafer substrate are disclosed. In one aspect, a protective layer is deposited over a surface of a wafer substrate using a process configured to produce substantially less damage in the wafer substrate than a first plasma-assisted deposition process. The protective layer is less than about 100 Angstroms thick. A barrier layer is deposited over the protective layer using the first plasma-assisted deposition process.

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